NSN 5962-01-293-1161

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Body Length:	
0.960 inches	
Body Width:	
Between 0.220 inche	s and 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Di	ssipation Rating:
950.0 milliwatts	
Operating Tempura	ture Range:
-55.0/+125.0 degrees	s celsius
Storage Tempuratu	re Range:
-65.0/+150.0 degrees	s celsius
Features Provided:	
Schottky and program	nmable and bipolar and monolithic and high impedance
Inclosure Material:	
Ceramic	
Inclosure Configura	tion:
Dual-in-line	
Output Logic Form:	
Transistor-transistor	ogic
Input Circuit Patterr	
12 input	
Case Outline Sourc	e And Designator:
D-6 mil-m-38510	
Terminal Surface Tr	eatment:
Solder	
Voltage Rating And	Type Per Characteristic:
-0.5 volts power sou	rce and 7.0 volts power source
Time Rating Per Ch	acteristic:
125.00 nanoseconds	propagation delay time, low to high level output and 125.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Typ	e:
Rom	
Test Data Documen	t:
96906-mil-std-883 sta	andard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And	Quantity:
18 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Demilitarization:

Yes - demil/mli

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